

BRCS18N20DP

Rev.C Feb.-2026

/ Descriptions

N TO-252

N-Channel MOSFET in a TO-252 Plastic Package.

/ Features

$V_{DS}=200V$ $I_D=18A$ $V_{GS}=\pm 20V$

$R_{DS(on)}@10V$ 170m (Type.130m)

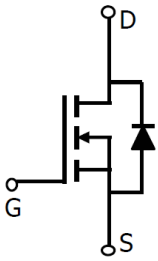
$R_{DS(on)}@4.5V$ 200m (Type.150m)

HF Product.

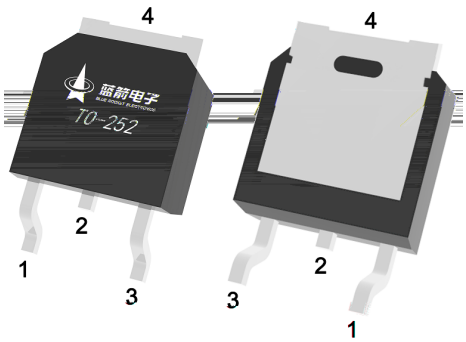
/ Applications

Networking, Load Switch, LED applications.

/ Equivalent Circuit



/ Pinning



PIN1 G

PIN 2 4 D

PIN 3 S

/ Marking

See Marking Instructions.

/ Absolute Maximum Ratings(Ta=25)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	200	V
Drain Current		$I_D(T_C=25)$	18	A
Drain Current - Pulsed		I_{DM}	43	A
Gate-Source Voltage		V_{GS}	± 20	V
Single Pulsed Avalanche Energy(L=10mH)		E_{AS}	125	mJ
Avalanche Current(L=10mH)		I_{AS}	9.5	A
Power Dissipation		$P_D(T_C=25)$	90	W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to 150	$^{\circ}C$
Maximum Junction-to-Ambient	t 10s	R_{JA}	20	$^{\circ}C/W$
Maximum Junction-to-Ambient	Steady-State		50	
Maximum Junction-to-Case	Steady-State	R_{JC}	1.39	

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$	$I_D=250\mu A$	200			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=200V$	$V_{GS}=0V$			1	μA
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 20V$	$V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$	$I_D=250\mu A$	1.0	1.5	2.0	V
Total gate charge	$R_{DS(on)}$	$V_{GS}=10V$	$I_D=10A$		130	170	m
		$V_{GS}=4.5V$	$I_D=10A$		150	200	m
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$	$I_S=1A$			1.2	V
Gate resistance	R_g	$V_{GS}=0V$ $f=1MHz$	$V_{DS}=0V,$		6.5		
Input Capacitance	C_{iss}	$V_{DS}=25V$ $f=1MHz$	$V_{GS}=0V$		830		pF
Output Capacitance	C_{oss}				150		
Reverse Transfer Capacitance	C_{rss}				65		
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=10V,$ $I_D=18A$	$V_{DS}=100V,$		27		nC
Total Gate Charge	$Q_{g(4.5V)}$				12		
Gate Source Charge	Q_{gs}				7		
Gate Drain Charge	Q_{gd}				3		

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $V_{DS}=75V$ $R_L=2.5$ $R_{GEN}=3$		8		ns
Turn-On Rise Time	t_r			10		
Turn-Off Delay Time	$t_{d(off)}$			30		
Turn-Off Fall Time	t_f			4		

/ Electrical Characteristic Curve

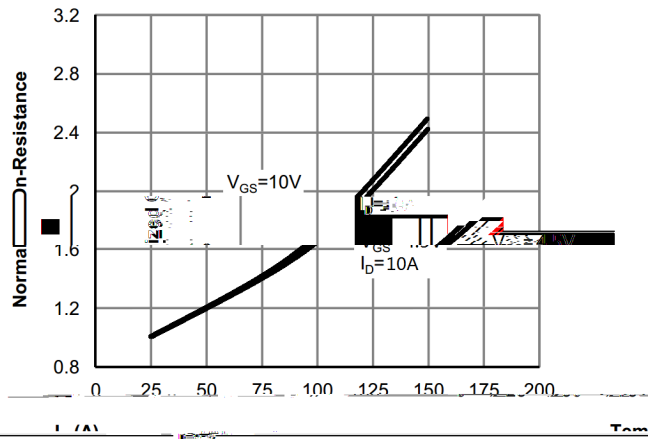
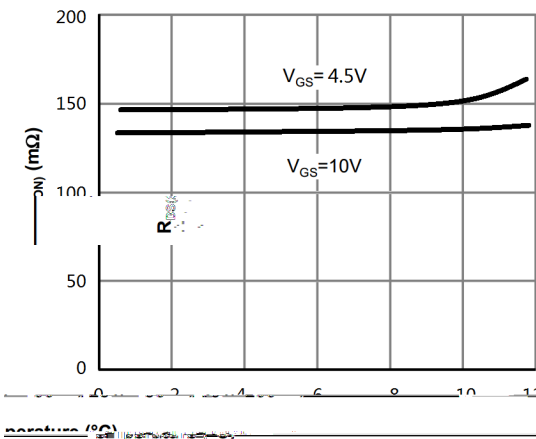
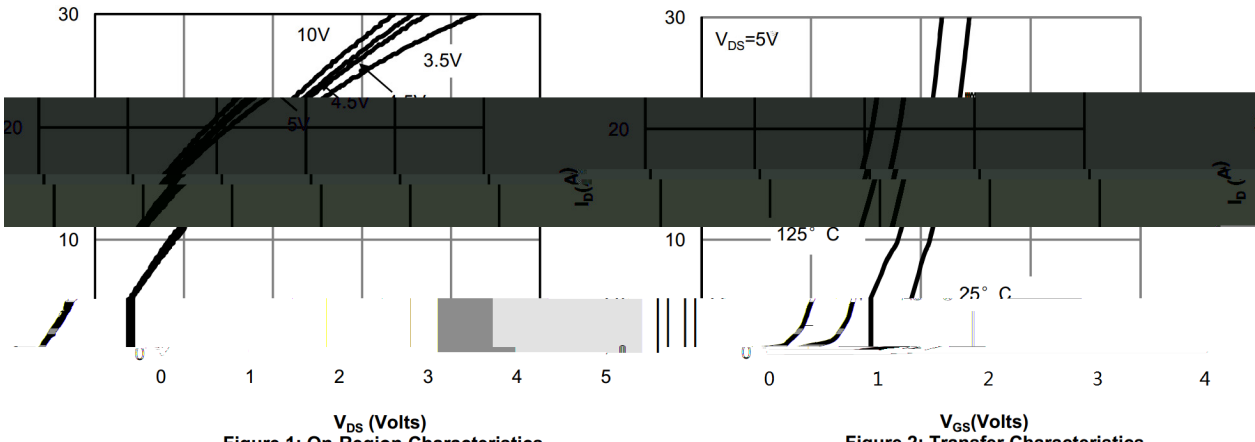
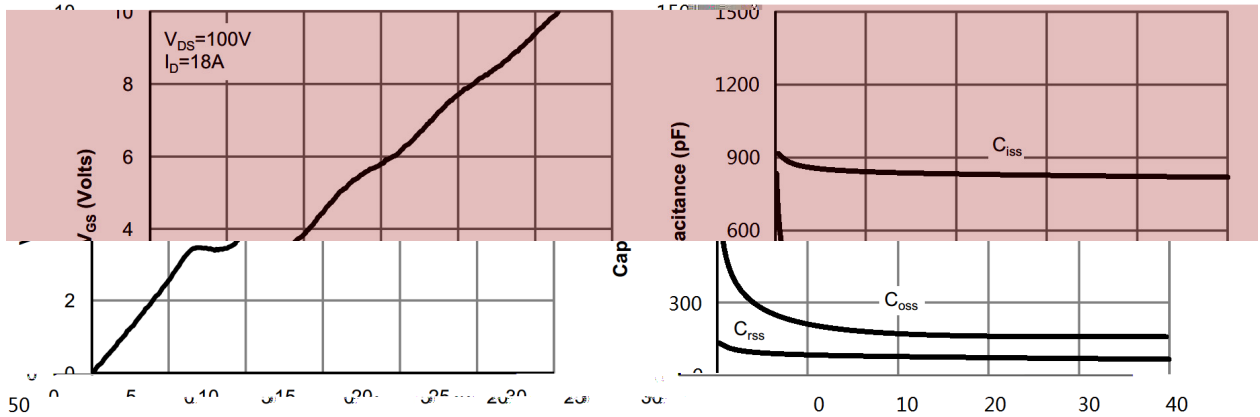


Figure 4: On-Resistance vs. Junction Temperature

Figure 3: On-Resistance vs. Drain Current and Gate



/ Electrical Characteristic Curve



DS (VOLTS)
Capacitance Characteristics

Figure 7: Gate-Charge Characteristics

Figure 8: Capacitance Characteristics

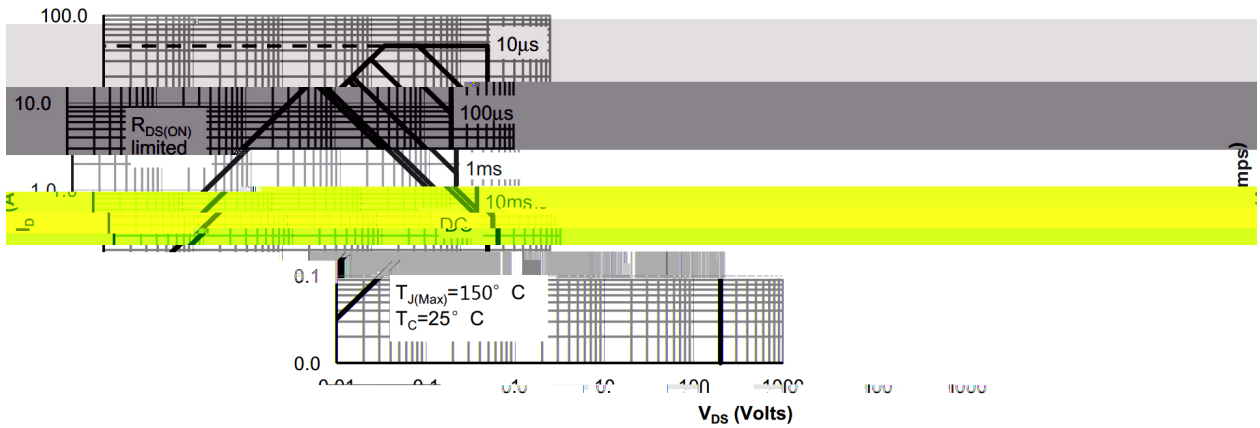


Figure 9: Maximum Forward Biased Safe Operating Area

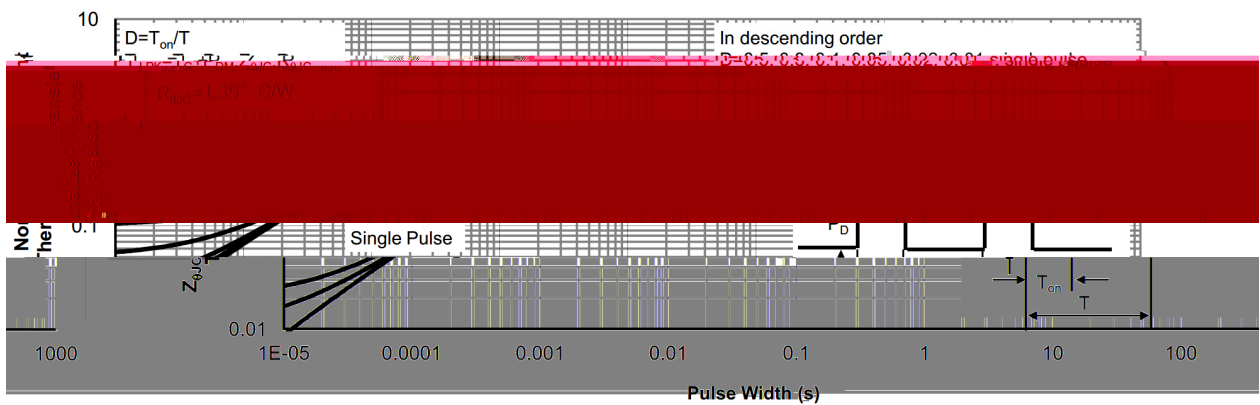
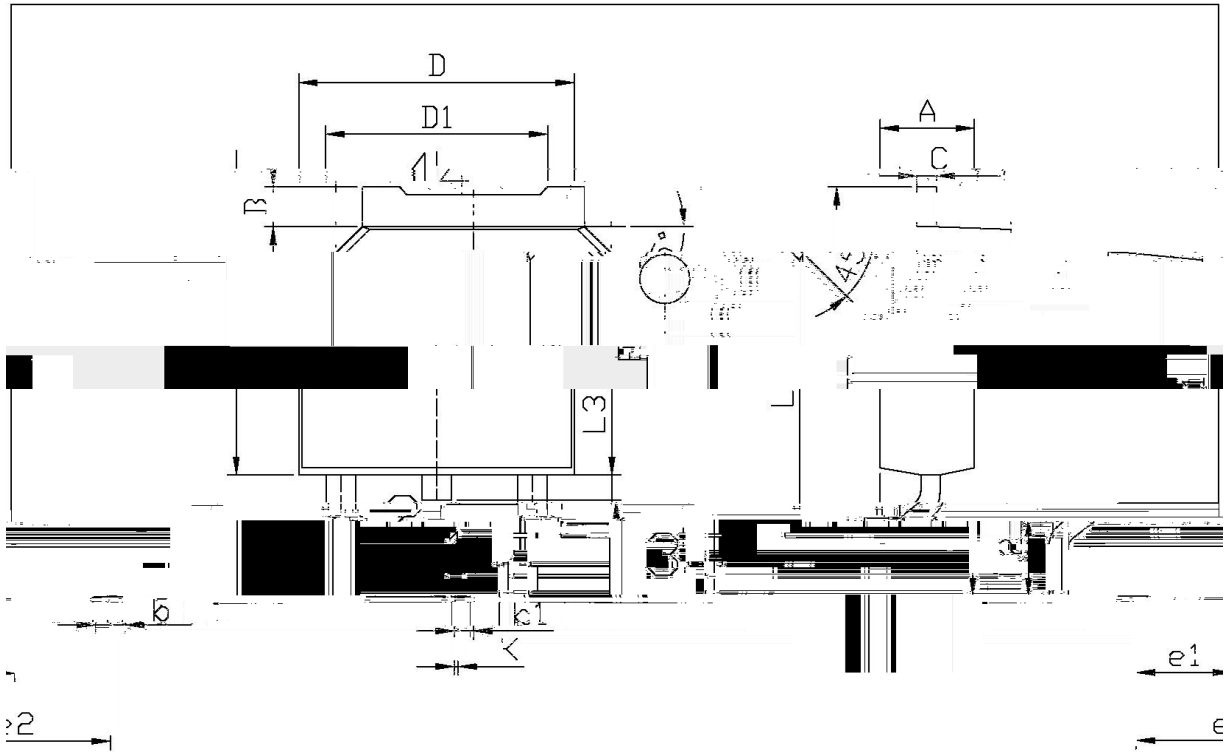


Figure 10: Normalized Maximum Transient Thermal Impedance

/ Package Dimensions

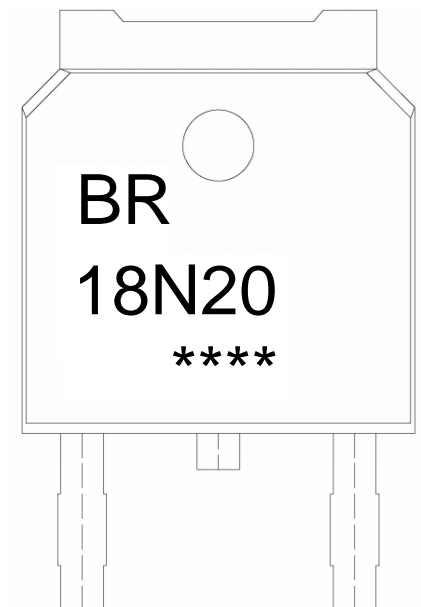


单位: mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min.	Max.		Min.	Max.
A	2.20	2.40	B	5.95	
e1	0.95	1.25	e	2.24	2.34
L3	0.70	0.90	L1	4.63	4.73
b	0.45	0.55	b1	9.85	10.35
C	0.45	0.45	D1	6.45	6.75
K	0.60	0.90	K1	0.50	0.50

T₀ = 25.2

/ Marking Instructions



Note:

BR: Company Code

18N20: Product Type Code

****: Lot No. Code, code change with Lot No.

() / Temperature Profile for IR Reflow Soldering(Pb-Free)

Note:

- | | | | |
|---|---------|-----------|---|
| 1 | 150 180 | 60 90sec; | 1.Preheating:150~180 , Time:60~90sec. |
| 2 | 245 5 | 5 0.5sec; | 2.Peak Temp.:245 5 , Duration:5 0.5sec. |
| 3 | 2 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditioneset Cond45D/Cp6duU51 Duration5